

What is claimed is:

An intermediate	microe	lectronic	package,	comprising

a first encapsulated die assembly having an active surface and a back surface, said first encapsulated die assembly including at least one first microelectronic die having an active surface and at least one side and a first packaging material adjacent said at least one first microelectronic die side; and

a second encapsulated die assembly having an active surface and a back surface, wherein said second encapsulated die assembly back surface is attached to said first encapsulated die assembly back surface said second encapsulated die assembly including at least one second microelectronic die having an active surface and at least one side and a second packaging material adjacent said at least one second microelectronic die side.

- 2. The intermediate microelectronic package of claim 1, wherein said first encapsulated die assembly active surface comprises said at least one first microelectronic die active surface and at least one surface of said first packaging material which is substantially planar to said first microelectronic die active surface.
- 3. The intermediate microelectronic package of claim 1, wherein said second encapsulated die assembly active surface comprises said at least one second microelectronic die active surface and at least one surface of said second packaging
- 4 material which is substantially planar to said first microelectronic die active surface.



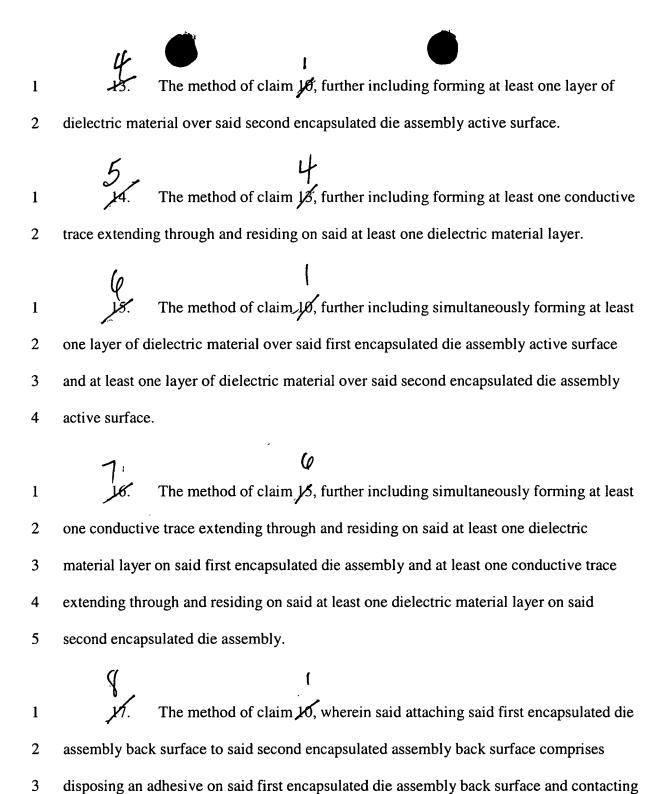


- 1 \ 4. The intermediate microelectronic package of claim 1, further including at
- 2 least one layer of dielectric material disposed over said first encapsulated die assembly
- active surface and at least one conductive trace extending through and residing on said at
- 4 least one dielectric material layer.
- 1 5. The intermediate microelectronic package of claim 1, further including at
- 2 least one layer of dielectric material disposed over said second encapsulated die assembly
- 3 active surface and at least one conductive trace extending through and residing on said at
- 4 least one dielectric material layer.
- 1 6. The intermediate microelectronic package of claim 1, further including an
- 2 adhesive material disposed between said first encapsulated die assembly back surface and
- 3 second encapsulated die assembly back surface.
- The intermediate microelectronic package of claim 6, wherein said
- 2 adhesive material is disposed in a desired patterned between said first encapsulated die
- 3 assembly back surface and second encapsulated die assembly back surface.
- 1 8. The intermediate microelectronic package of claim 1, wherein said first
- 2 and said second packaging material comprises an encapsulation material.

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	1	9. The intermediate microelectronic package of claim 1, wherein said first
B	2	and said second packaging material comprises a microelectronic package core and an
V	3	encapsulation material.
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5411	1	10. A method of fabricating microelectronic dice, comprising:
12	2	providing a first encapsulated die assembly having an active surface and a back
117	3	surface, said first encapsulated die assembly including at least one first microelectronic
,	4	die having an active surface and at least one side and a first packaging material adjacent
	5	said at least one first microelectronic die side; and
5	6	providing a second encapsulated die assembly having an active surface and a back
oestago	7	surface, said second encapsulated die assembly including at least one second
	8	microelectronic die having an active surface and at least one side and a second packaging
<u>.</u> .0	9	material adjacent said at least one second microelectronic die side; and
: (3)	10	attaching said first encapsulated die assembly back surface to said second
	11	encapsulated assembly back surface.
	<u> </u>	
	1	The method of claim 10, further including forming at least one layer of
	2	dielectric material over said first encapsulated die assembly active surface.

trace extending through and residing on said at least one dielectric material layer.

The method of claim \mathcal{N} , further including forming at least one conductive



said second encapsulated assembly back surface with said adhesive.

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1	184	The method of claim 17, wherein said disposing an adhesive on said first
2	encapsulated	die assembly back surface comprises patterning said adhesive on said first
3	encapsulated	die assembly back surface.
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1	J19.	The method of claim 18, wherein said patterning said adhesive comprises
2	placing at lea	st one adhesive line between a first microelectronic die and an adjacent
3	microelectron	ic die on said first encapsulated die assembly back surface.
	11	10
1	,2 0 .	The method of claim 19, further including dicing said first encapsulated
2	die assembly	and said second encapsulated die assembly such that said dicing removes
3	said at least o	ne adhesive line.
1,	21.	The method of claim 10, wherein said providing a first encapsulated die
2	assembly con	nprises:
3		providing at least one first microelectronic die having an active surface
4	and at	least one side;
5		abutting a protective film against said at least one first microelectronic die
6	active	surface;
7		encapsulating said at least one microelectronic die with an encapsulation
8	mater	ial adjacent said at least one first microelectronic die side, wherein said
9	encap	sulation material provides at least one surface of said encapsulation material

substantially planar to said first microelectronic die active surface; and

to form a first encapsulated die active surface and a first encapsulated die 9 back surface; 10 11 forming a second encapsulated die assembly comprising: providing at least one second microelectronic die having an active 12 surface and at least one side; 13 abutting a protective film against said at least one second 14 microelectronic die active surface; and 15 16 encapsulating said at least one microelectronic die with an 17 packaging material adjacent said at least one second microelectronic die side to form a second encapsulated die active surface and a second 18 M 19 encapsulated die back sufface; and attaching said first encapsulated die assembly back surface to said second 20 21 encapsulated assembly back surface. 15 Ш The method of claim 23, further including forming at least one layer of -24. 1 2 dielectric material over said first encapsulated die assembly active surface. 16 The method of claim 23, further including forming at least one conductive 1 2 trace extending through and residing on said at least one dielectric material layer.

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dielectric material over said second encapsulated die assembly active surface.

The method of claim 23, further including forming at least one layer of

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1	ZX.	The method of claim 23, further including forming at least one conductive
2	trace extendi	ng through and residing on said at least one dielectric material layer.

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The method of claim 23, further including simultaneously forming at least 1 2 one layer of dielectric material over said first encapsulated die assembly active surface 3 and at least one layer of dielectric material over said second encapsulated die assembly 4 active surface.

19 The method of claim 28, further including simultaneously forming at least one conductive trace extending through and residing on said at least one dielectric material layer on said first encapsulated die assembly and at least one conductive trace extending through and residing on said at least one dielectric material layer on said second encapsulated die assembly.

The method of claim 23, wherein said attaching said first encapsulated die 30. assembly back surface to said second encapsulated assembly back surface comprises disposing an adhesive on said first encapsulated die assembly back surface and contacting said second encapsulated assembly back surface with said adhesive.

The method of claim 30, wherein said disposing an adhesive on said first
osulated die assembly back surface comprises patterning said adhesive on said first
osulated die assembly back surface.
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1	The method of claim 31, wherein said patterning said adhesive comprises
2	placing at least one adhesive line between a first microelectronic die and an adjacent
3	microelectronic die on said first encapsulated die assembly back surface.

The method of claim 32, further including dicing said first encapsulated die assembly and said second encapsulated die assembly such that said dicing removes said at least one adhesive line.